

# **HIGH PERFORMANCE CMOS DEVICE STRUCTURES AND METHOD OF MANUFACTURE**

## **Abstract**

A semiconductor device structure includes at least two field effect transistors formed on same substrate, the first field effect transistor includes a spacer having a first width, the second field effect transistor includes a compressive spacer having a second width, the first width being different than said second width. Preferably, the first width is narrower than the second width. A tensile stress dielectric film forms a barrier etch stop layer over the transistors.